



Design and Demonstration of 2.5D Glass Interposer BGA package with 2 μm ML RDL

Students- Pratik Nimbalkar, Omkar Gupte, Siddharth Ravichandran, Shreya Dwarakanath, Bartlet DeProspo, Rui Zhang

Faculty- Prof. Swaminathan, Prof. Tummala, Dr. Mohan Kathaperumal, Dr. Fuhan Liu, Dr. Vanessa Smet

Industry Partners: Atsushi Kubo (TOK), Takenori Kakutani (Taiyo), Nobuo Ogura (Nagase), Murata, Ajinomoto, Corning, Disco, Schott, AMAT, Atotech, SKC, Samtec, Intel, Evatec, Canon

Goals and Objectives



Enabling Basic Technology Targets (2018-2020)

Parameter Objective **Prior Art (Silicon Interposer)** Materials Low-k dielectrics: $k \sim 3$ SiO₂: k ~ 3.8-4.0 **Double Sided SAP** Wafer Scale BEOL Process Interconnect 225 IOs/mm/layer (Low R and 250-400 IOs/mm/layer (High R IO density C) and C) Bump pitch (Chip 35 um (TCB) 45 um (TCB) level) Body Size (Board 40 mm x 50 mm (Mass 28 mm x 36 mm (Mass Reflow) Reflow) Level) Advanced Direct Cu plated Thermal Std. Heat Sink heat sink Low (Panel-Scale Processes) High (Wafer-scale processes) **Relative Cost** Large Body Size Feasible Small Body Size feasible Board Level Reliability **Direct Board Attach** Need Organic Package substrate

- RDL interconnects approaching BEOL RDL with lower R and C
- Fine pitch chip-level interconnect
- **Direct attachment** to board
- Low-cost large body size substrate



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Prior Work





 High R and C RDL interconnects
Board Level Reliability (combined with thick organic substrate)
High Cost for Large Body Size

C. Lee et al., "An Overview of the Development of a GPU with integrated HBM on Silicon Interposer", ECTC, 2016, 1439.





- High R and C RDL and Long interconnects
- Board Level Reliability (combined with thick organic substrate)
- Large Body Size Feasible

R. Mahajan et al., "Embedded Multi-Die Interconnect Bridge (EMIB) – A High Density, High Bandwidth Packaging Interconnect", ECTC, 2016, 557.



 Low R and C RDL interconnects
Z-height (thick organic core)
Large Body Size Feasible
of fine pitch Metal Layers (RDL yield/cost) > 4

K. Oi et al., "Development of New 2.5D Package with Novel Integrated Organic Interposer Substrate with Ultra-fine Wiring and High Density Bumps", ECTC, 2016, 557.

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Technical Approach

Processes Panel-Scale Semi-Additive Process

 Surface Planarization for High Yield RDL formation

End Point Seed Etch Detection

 \triangleright



Materials

- **Ultra-Thin, Low D_k Dielectrics**
 - Panel Processable
 - Low CTE, Low Modulus, High Elongation to Break

Reliability

> RDL Reliability

- Fine pitch traces and u-vias
- Multi-Layer RDL Reliability on Glass
- > Interconnect
 - Chip Level interconnects at 35 um pitch
 - Board Level with 7 ppm/K CTE Glass core



Assembly

- Chip-level interconnect
 - TCB Cu pillar
- Board-level interconnect
 - Large body 30 mm x 40 mm SMT

Low Cost

- Low Cost, Panel Scale Processes
- Large Body Size Substrates

Interconnects

Low R, Low C 2 um Multi-Layer RDL with 50 ohms impedance matching

Thermal

Advanced Direct Cu plated heat sinks

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TGV map for 6"x6" glass panel

TGV map for single interposer

- 100 μm TGVs with pitch varying from 200-500 μm
- Optimized through via filing for vias down to 50 μm diameter and 300 μm substrate (6:1 aspect ratio)
- Study of metallization of TGVs to be done

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Photo-Imageable Dielectric for fine line RDL

- Novel photo-dielectric for high resolution
- Good balance between low CTE and high resolution
- With low % elongation to break and smaller tensile strength, the goal is to maintain via taper angles between 64°-90°
- Low roughness thus optimization of sputtering needed for better adhesion and reliability

Conditions-

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1) Plasma Treatment:

- Ar plasma- 8.5 mins
- O2 plasma- 2 mins
- 2) Pre-bake: 125°C for 30mins in vacuum
- 3) Sputtering chamber pressure: 10E-6 Torr

Lead: Kenny K (Taiyo), Pratik

		Via T	op: 3 ur	n	Properties	Uni	t P	DM
	<				Tg (@TMA)	(deş	z.C) 18	80 - 185
				1	CTE alpha 1	(ppi	m) 3 0	0-35
DM		Plate	d Copper	PDM	Elastic Modu	lus (GP	'a) 3 .	5 - 4.0
	PDIVI				Tensile Stren	gth (MI	Pa) 9	0 - 95
	Via	Bott	.om: 2 u	m	Elongation	(%)	5.	5 - 6.0
		<	>		Dk (10GHz)		3.	.3
					Df(10GHz)		0.	.019
WD	mag t	11: 9/20/2011) HV 0. 17	2_m	Water absorp	tion (%)	0.	.84
	I and (Creme)				Average- 14 Minimum- 1 Maximum- 2	.2 N/cm .3.1 N/cm 14.9 N/cm		
		-	0	1	2	3	4	5

Position (Centimeters)

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ML-RDL residual stress analysis





Lead: Pratik

Schematic stack up of dummy ML RDL



- A thicker dielectric provides more stress relaxation as compared to thin dielectric
- For a dielectric having lower tensile modulus, stress is lower upto formation of the first metal layer
- As the number of metal layers goes on increasing, the stress starts levelling out

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Lead: Pratik (Fabrication) Omkar (BGA Balling) Disco (Dicing)



Objective: Understand challenges and optimize the dicing conditions for glass BGA package with no over mold



- Test Three Different Glass CTEs (3.4, 7.8 and 9 ppm/K) replicating Mechanical TV
 - 300 μm thick glass with dielectric stacks
 - Only top and bottom metal layers
 - Fabrication completed

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Georgia Results: Mechanical Test Vehicle -Board-Level Reliability





Lead: Pratik (Fa<mark>brication)</mark> Vanessa (Assembly)

- ✓ Test three different glass CTEs (3.4, 7.8 and 9 ppm/K) for board-level reliability
 - 300 µm
 - No TGVs

- Electrical routing structures to test board-level interconnections post thermal cycling reliability

Results: Prior Work



Reliability modeling for 2.5D glass interposer with 4 ML symmetric RDL stack-up



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Glass CTE (ppm/K)	Package size (mm)	BGA diameter (um)	BGA pitch	Package thickness (um)	Nf (Coffin Manson)	Nf (Engelmaier Wild)			
3.4	40 x 30	350	650	300	106	104			
9	40 x 30	350	650	300	918	1389			
9	40 x 30	350	650	100	1162	1844			
9.8	40 x 30	350	650	300	1099	1724			
9	50 x 40	350	650	300	928	1408			
9	60 x 50	350	650	300	1097	1721			
9	50 x 40	500	800	300	1395	2295			
7.8	50 x 40	500	800	300	1283	2076			
3.4	50 x 40	500	800	300	520	703			
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Summary



- **TGV des**ign is complete
- Optimized sputtering conditions for improved adhesion and reliability of RDL
- Dicing test vehicle fabrication has been completed and panel sent to Disco for dicing test on 10/30/2019
- Mechanical test vehicle fabrication is ongoing
- Thermomechanical modeling: packages with 8 ML asymmetric stack-up and high CTE glass core (7.8 and 9 ppm/K) expected to pass 1000 thermal cycles



Schedule



